

Application Serial No. 10/603,306
Reply to Office Action of September 13, 2004

PATENT
Docket: CU-3271

Amendments To The Specification

Please replace paragraph in the Specification page 7, lines 15-24 with the following amended paragraph:

Referring to FIG. 1c, a sacrificing oxidation film 7 is deposited on the contact plug 6 and the capping nitride film ~~7~~ 4 to a thickness of 5000 to 20000 Å in order to form a storage electrode having a cylindrical shape. Thereafter, the sacrificing oxidation film 7 is etched to form a trench 8 through which the contact plug 6 and the adjoining nitride film positions are exposed. Subsequently, a conductive film for storage electrode, for example, a polysilicon film 9 is deposited on the trench surface 8 and the sacrificing oxidation film 7.